

To our customers,

Old Company Name in Catalogs and Other Documents

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Renesas Electronics website: <http://www.renesas.com>

April 1st, 2010
Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (<http://www.renesas.com>)

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NPN SILICON RF TRANSISTOR

Phase-out/Discontinued

NE662M03

**NPN SILICON RF TRANSISTOR FOR
LOW NOISE · HIGH-GAIN AMPLIFICATION
FLAT-LEAD 3-PIN THIN-TYPE ULTRA SUPER MINIMOLD**

FEATURES

- ★ • Ideal for low noise · high-gain amplification and high-frequency oscillation
NF = 1.2 dB TYP. @ $V_{CE} = 2\text{ V}$, $I_c = 5\text{ mA}$, $f = 2\text{ GHz}$
- MSG = 15 dB TYP. @ $V_{CE} = 2\text{ V}$, $I_c = 20\text{ mA}$, $f = 2\text{ GHz}$
- $|S_{21e}|^2 = 12.5\text{ dB TYP. @ } V_{CE} = 2\text{ V}$, $I_c = 20\text{ mA}$, $f = 2\text{ GHz}$
- $f_T = 21\text{ GHz TYP. @ } V_{CE} = 2\text{ V}$, $I_c = 20\text{ mA}$, $f = 2\text{ GHz}$
- Flat-lead 3-pin thin-type ultra super minimold package

ORDERING INFORMATION

Part Number	Quantity	Supplying Form
NE662M03	50 pcs (Non reel)	• 8 mm wide embossed taping • Pin 3 (Collector) face the perforation side of the tape
NE662M03-T1	3 kpcs/reel	

Remark To order evaluation samples, contact your nearby sales office.
The unit sample quantity is 50 pcs.

ABSOLUTE MAXIMUM RATINGS ($T_A = +25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	15	V
Collector to Emitter Voltage	V_{CEO}	3.3	V
Emitter to Base Voltage	V_{EBO}	1.5	V
Collector Current	I_c	35	mA
Total Power Dissipation	P_{tot}^{Note}	115	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +150	$^\circ\text{C}$

Note Mounted on $1.08\text{ cm}^2 \times 1.0\text{ mm}$ (t) glass epoxy PCB

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

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Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

ELECTRICAL CHARACTERISTICS (T_A = +25°C)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Collector Cut-off Current	I _{CBO}	V _{CB} = 5 V, I _E = 0 mA	–	–	200	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 1 V, I _C = 0 mA	–	–	200	nA
DC Current Gain	h _{FE} ^{Note 1}	V _{CE} = 2 V, I _C = 5 mA	60	80	100	–
RF Characteristics						
Gain Bandwidth Product	f _T	V _{CE} = 2 V, I _C = 20 mA, f = 2 GHz	–	21	–	GHz
Insertion Power Gain	S _{21e} ²	V _{CE} = 2 V, I _C = 20 mA, f = 2 GHz	10.0	12.5	–	dB
Noise Figure	NF	V _{CE} = 2 V, I _C = 5 mA, f = 2 GHz, Z _S = Z _{opt}	–	1.2	1.5	dB
Reverse Transfer Capacitance	C _{re} ^{Note 2}	V _{CB} = 2 V, I _E = 0 mA, f = 1 MHz	–	0.21	0.3	pF
Maximum Available Power Gain	MAG ^{Note 3}	V _{CE} = 2 V, I _C = 20 mA, f = 2 GHz	–	14	–	dB
Maximum Stable Power Gain	MSG ^{Note 4}	V _{CE} = 2 V, I _C = 20 mA, f = 2 GHz	–	15	–	dB

- Notes** 1. Pulse measurement: PW ≤ 350 μs, Duty Cycle ≤ 2%
 2. Collector to base capacitance when the emitter grounded

3. $MAG = \left| \frac{S_{21}}{S_{12}} \right| (K - \sqrt{K^2 - 1})$

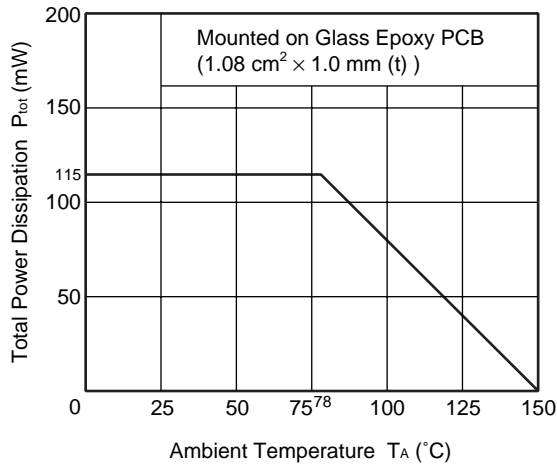
4. $MSG = \left| \frac{S_{21}}{S_{12}} \right|$

h_{FE} CLASSIFICATION

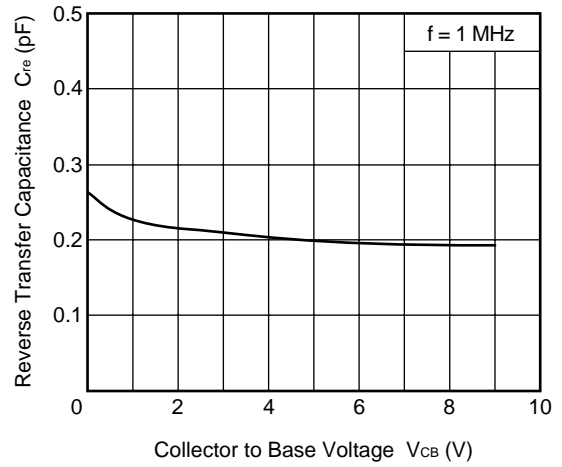
Rank	FB
Marking	UF
h _{FE} Value	60 to 100

★ TYPICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise specified)

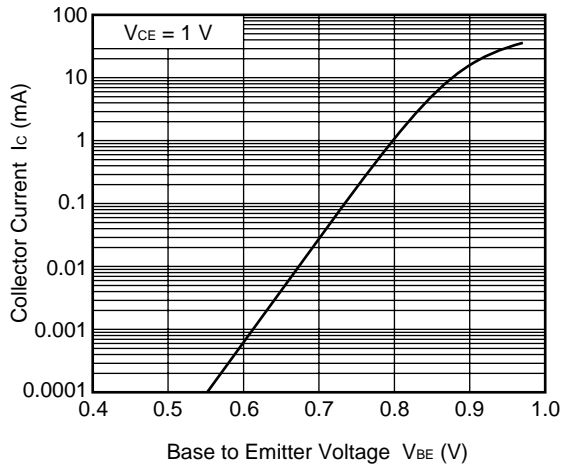
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



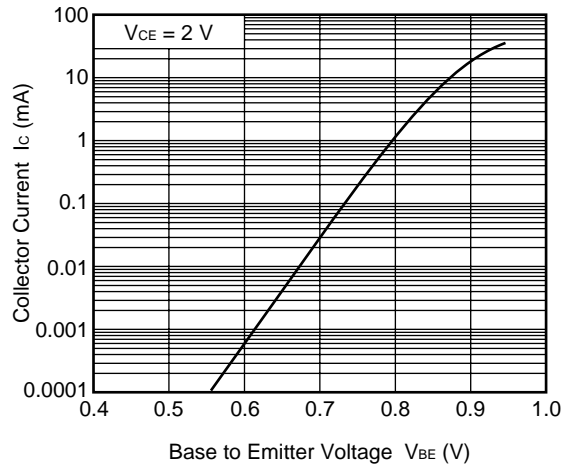
REVERSE TRANSFER CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



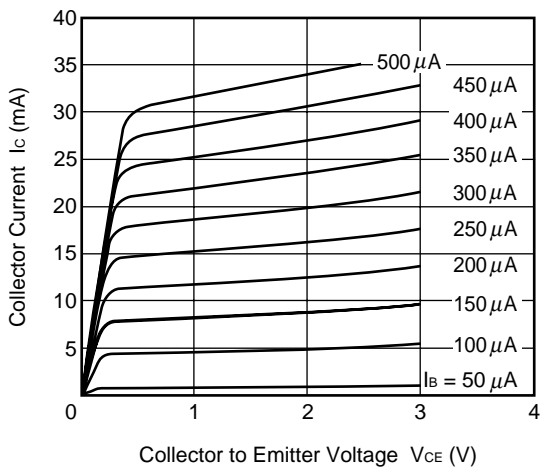
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



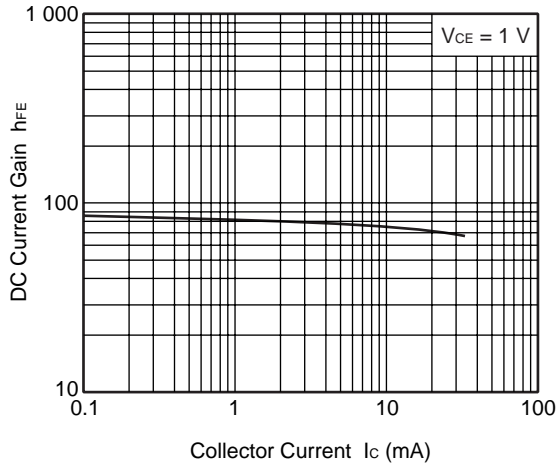
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



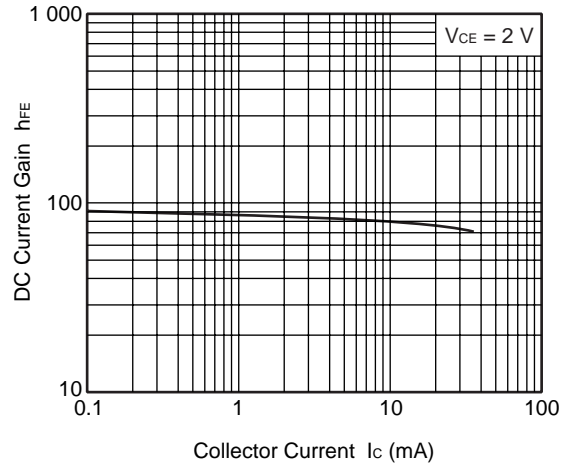
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



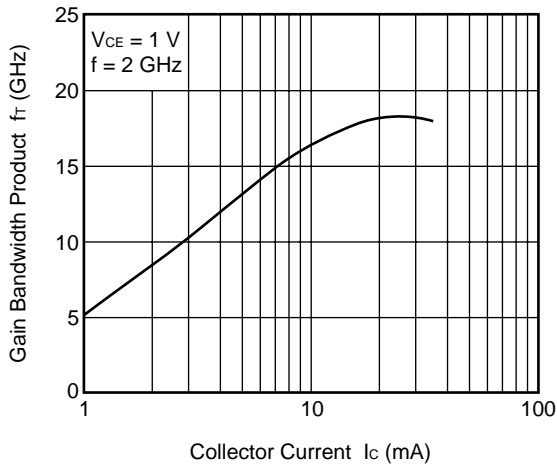
DC CURRENT GAIN vs. COLLECTOR CURRENT



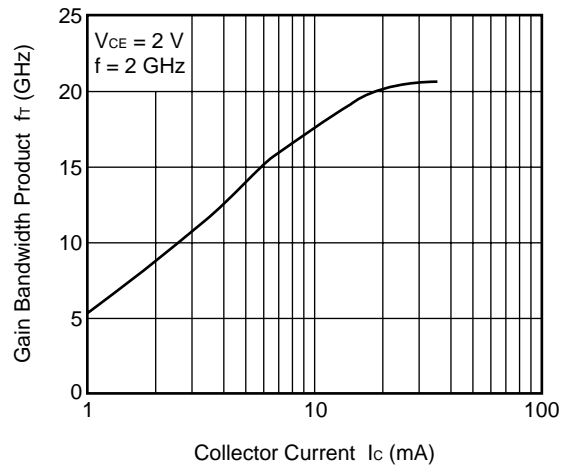
DC CURRENT GAIN vs. COLLECTOR CURRENT



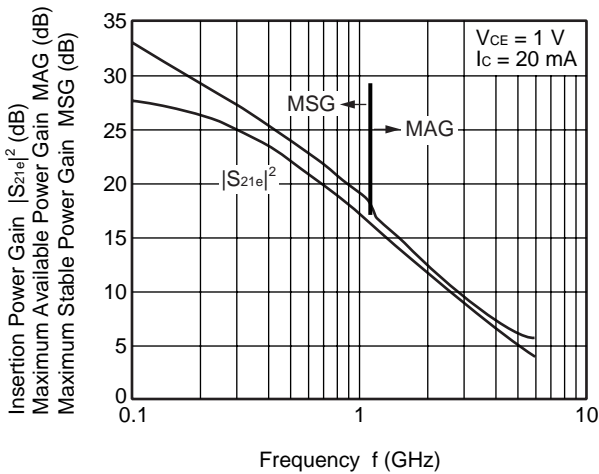
GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT



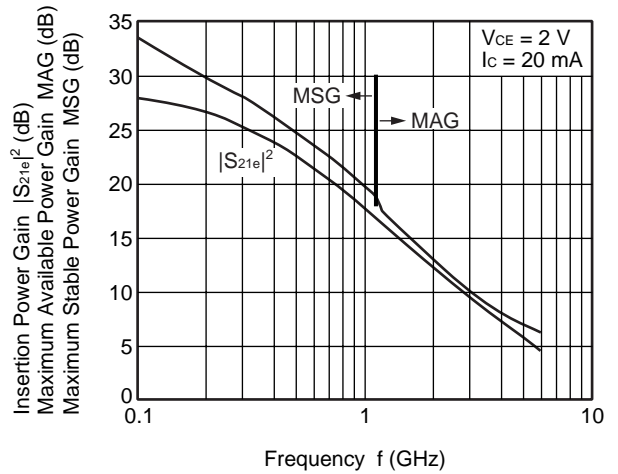
GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT



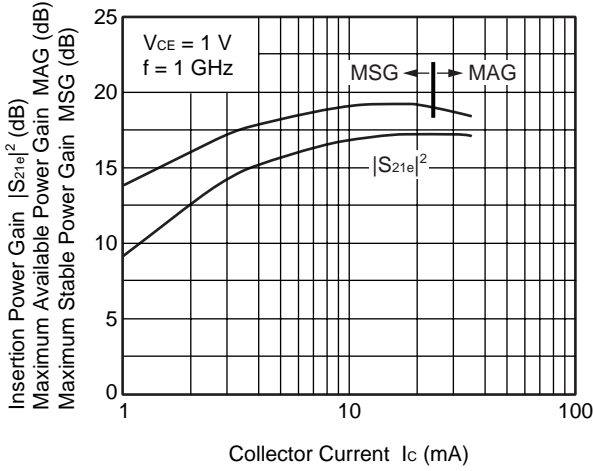
INSERTION POWER GAIN, MAG, MSG vs. FREQUENCY



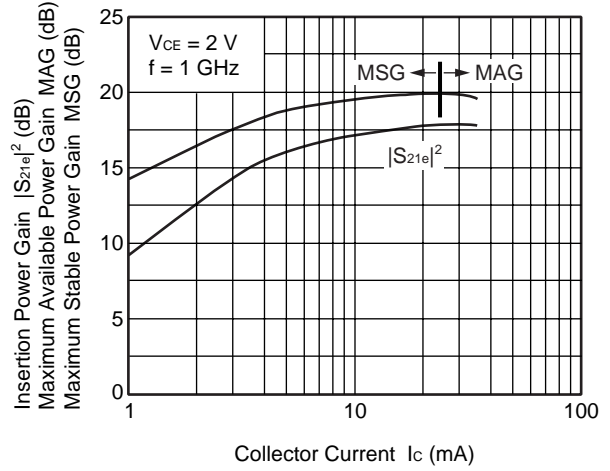
INSERTION POWER GAIN, MAG, MSG vs. FREQUENCY



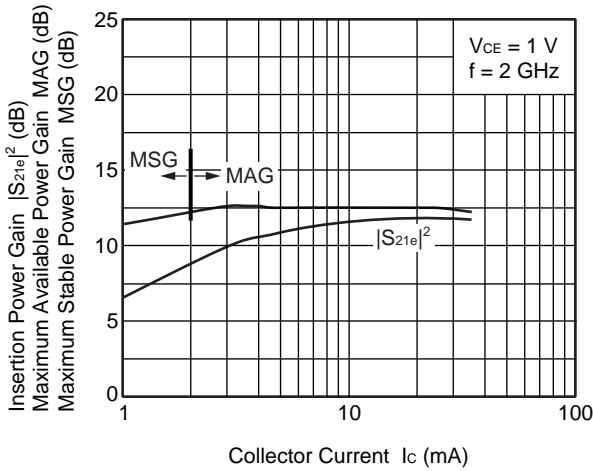
INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT



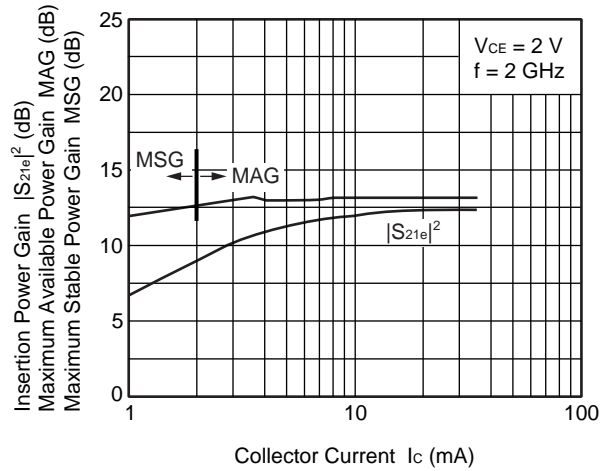
INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT



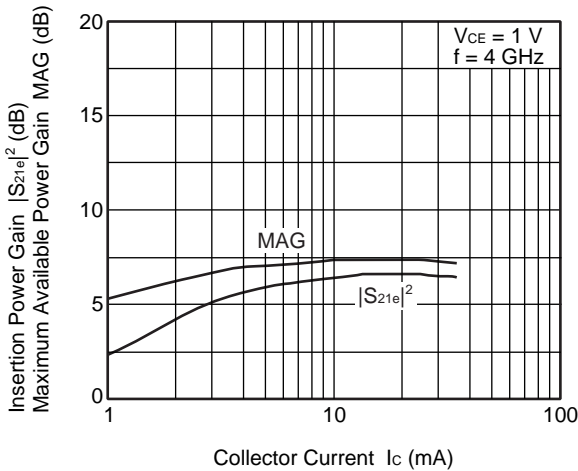
INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT



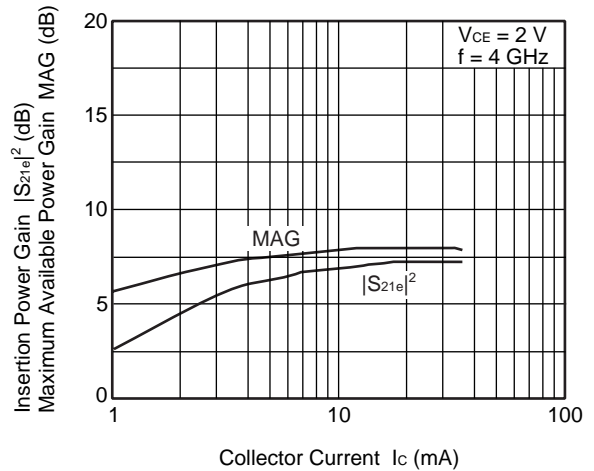
INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT



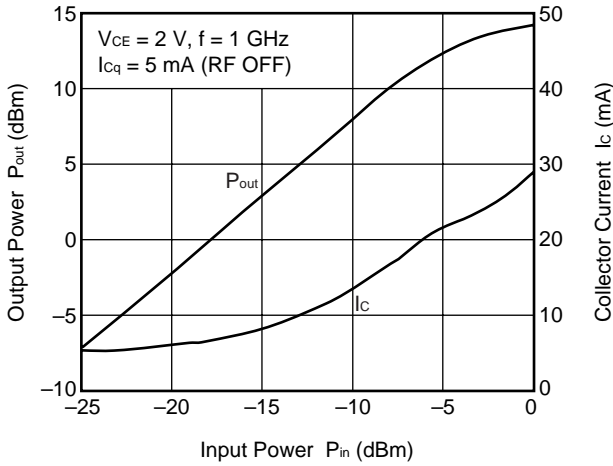
INSERTION POWER GAIN, MAG vs. COLLECTOR CURRENT



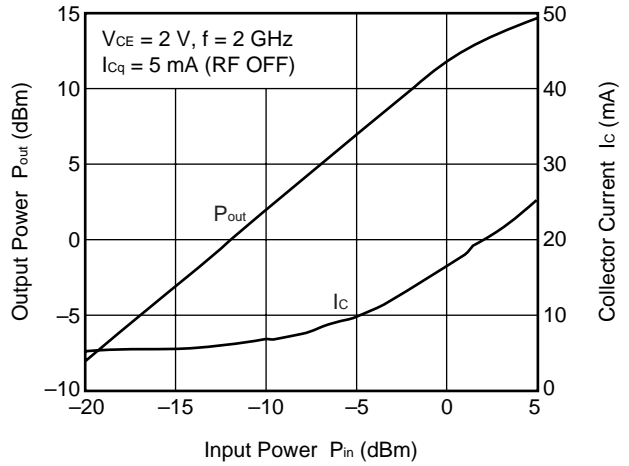
INSERTION POWER GAIN, MAG vs. COLLECTOR CURRENT



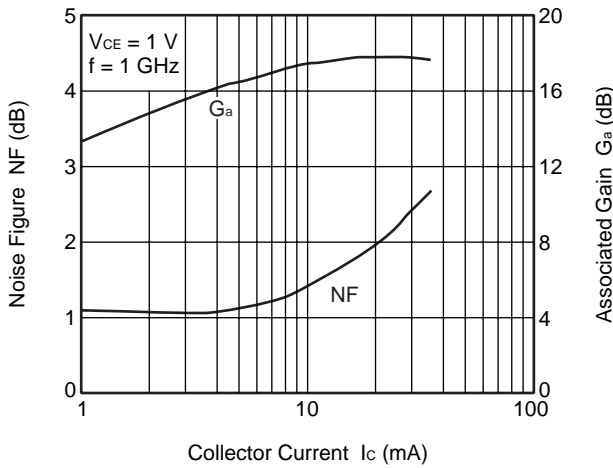
OUTPUT POWER, COLLECTOR CURRENT vs. INPUT POWER



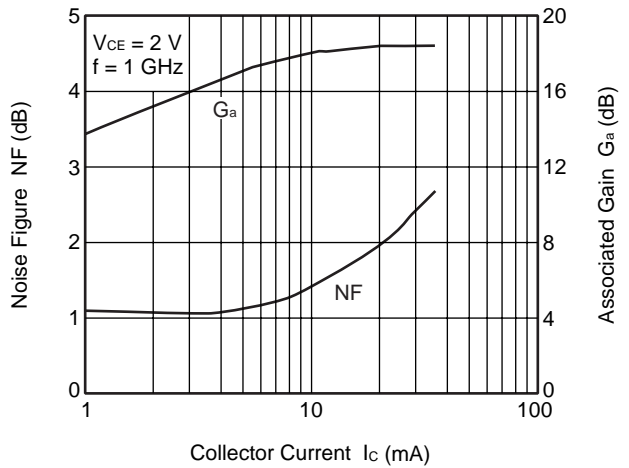
OUTPUT POWER, COLLECTOR CURRENT vs. INPUT POWER



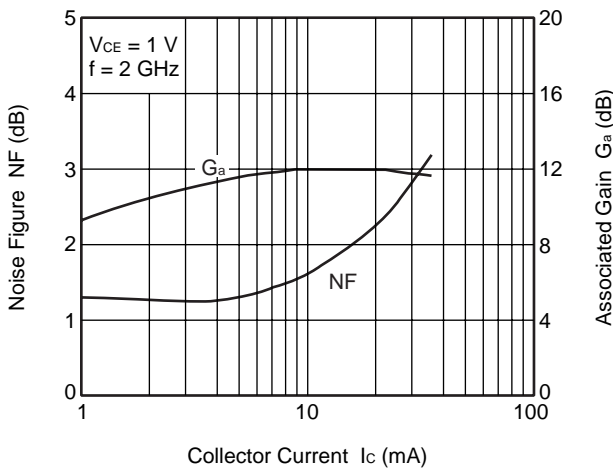
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



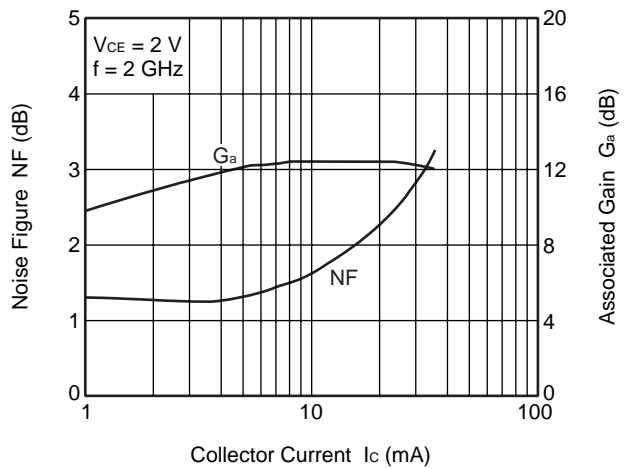
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



Remark The graphs indicate nominal characteristics.

S-PARAMETERS

S-parameters/Noise parameters are provided on the NEC Compound Semiconductor Devices Web site in a form (S2P) that enables direct import to a microwave circuit simulator without keyboard input.

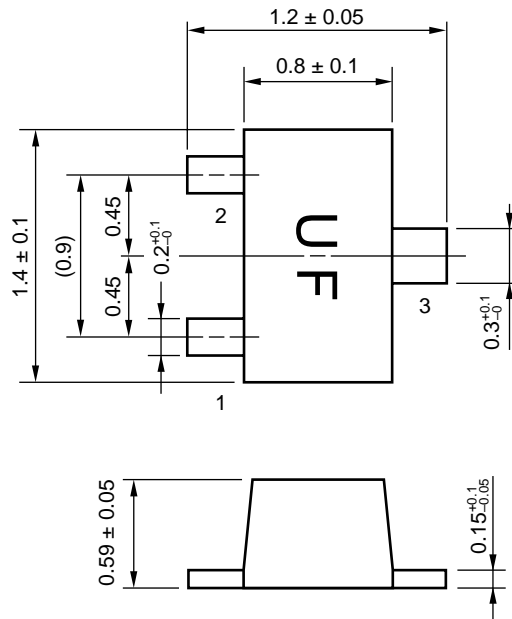
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[RF and Microwave] → [Device Parameters]

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PACKAGE DIMENSIONS

FLAT-LEAD 3-PIN THIN-TYPE ULTRA SUPER MINIMOLD (UNIT: mm)



PIN CONNECTIONS

- 1. Emitter
- 2. Base
- 3. Collector

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